

#8/B 4-28-03 Mulish

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: Fumikazu YAMAKI et al.

Group Art Unit: 2826

Serial No.: 10/035,444

Examiner: Tan N. Tran

Filed: January 4, 2002

P.T.O. Confirmation No.: 3015

For: SEMICONDUCTOR DEVICE WITH A SUPER LATTICE BUFFER

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents Washington, D.C. 20231

April 21, 2003

Sir:

In response to the Office Action dated December 20, 2002, extended to April 20, 2003 by a one-month Petition for Extension of Time, please amend the above-identified application as follows:

CLEAN VERSION OF AMENDMENTS

IN THE CLAIMS:

Please cancel claim 11 without prejudice or disclaimer.

Please amend claims 1-10 as follows:

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1. (Amended) A high power semiconductor device for a radio communication system,

comprising:

a compound semiconductor substrate having a resistivity less than 1.0 x 10⁸ Ohm-cm at least at surface thereof;

a buffer layer formed on the compound semiconductor substrate and having a super lattice